

# Current/Voltage Conversion Amplifier for CD Optical Pickups Monolithic IC MM1729XB

## Outline

This IC is a current/voltage converting amplifier developed for compact disc optical pickups including photodiode elements.

## Features

1. High speed frequency response       $f_c=8\text{MHz}$  typ.
2. High sensitivity                         $37\text{mV}/\mu\text{W}$  typ.
3. Wide temperature range                 $-20\sim+75^\circ\text{C}$
4. High-performance, compact transparent molded package.

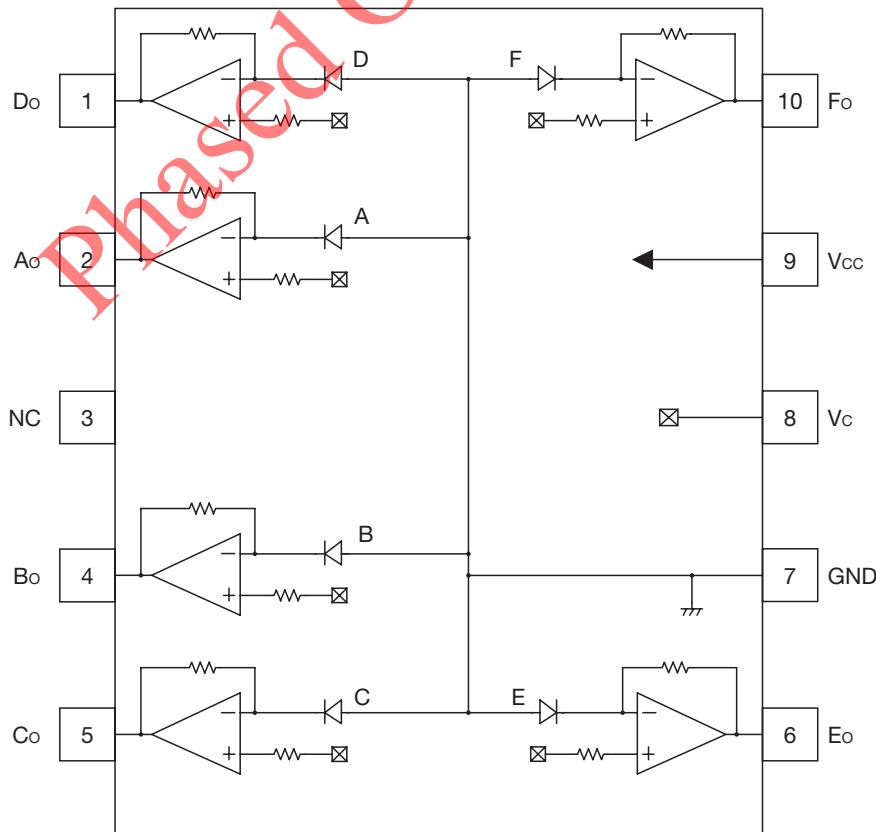
## Package

CMP-10C 4.0×5.0mm compact transparent molded package

## Applications

1. Music CD players
2. Portable music CD players

## Block Diagram



A, B, C, D, E, and F are photodiodes

## Pin Description

| Pin No.          | Pin name             | I/O    | Functions   | Internal equivalent circuit diagram |
|------------------|----------------------|--------|---|-------------------------------------|
| 1<br>2<br>4<br>5 | Do<br>Ao<br>Bo<br>Co | Output | Output of electrical signal converted from optical signals. |                                     |
| 3                | NC                   |        |   |                                     |
| 6<br>10          | Eo<br>Fo             | Output | Output of electrical signal converted from optical signals. |                                     |
| 7                | GND                  |        | GND Pin.  |                                     |
| 8                | Vc                   | Input  | Center voltage input pin.                                   |                                     |
| 9                | Vcc                  | Input  | Power voltage supply pin.                                   |                                     |

## Absolute Maximum Ratings (Ta=25°C)

| Item                  | Symbol               | Ratings | Units |
|-----------------------|----------------------|---------|-------|
| Storage temperature   | T <sub>STG</sub>     | -40~+85 | °C    |
| Operating temperature | T <sub>OPR</sub>     | -20~+75 | °C    |
| Supply voltage        | V <sub>CC</sub> max. | 6       | V     |
| Allowable loss        | P <sub>d</sub>       | 200     | mW    |

## Recommended Operating Conditions

| Item                                     | Symbol            | Ratings           | Units |
|--|-------------------|-------------------|-------|
| V <sub>CC</sub> Operating supply voltage | V <sub>CCOP</sub> | 2.80~5.50         | V     |
| V <sub>C</sub> Operating supply voltage  | V <sub>COP</sub>  | 1.40~2.75 (note1) | V     |
| Operating temperature                    | T <sub>OPR</sub>  | -20~+75           | °C    |

note 1 : V<sub>COP</sub>= 1/2 V<sub>CCOP</sub>

## Electrical Characteristics (Except where noted otherwise Ta=25°C, V<sub>CC</sub>=5V, V<sub>C</sub>=2.5V)

| Item                                    | Symbol            | Measurement conditions                          | Min. | Typ. | Max. | Units |
|---|-------------------|---|------|------|------|-------|
| Current consumption                     | I <sub>CC</sub>   | In dark condition                               |      | 4.0  | 6.0  | mA    |
| Output offset voltage<br>(note 1-1)     | V <sub>OFF</sub>  | A~D In dark condition                           | -10  | 0    | 10   | mV    |
|   |                   | E, F In dark condition                          | -10  | 0    | 10   | mV    |
| Output offset<br>voltage difference     | ΔV <sub>OFF</sub> | (A+B) - (C+D) In dark condition                 | -10  | 0    | 10   | mV    |
|   |                   | (A+C) - (B+D) In dark condition                 | -10  | 0    | 10   | mV    |
|   |                   | (A+D) - (B+C) In dark condition                 | -10  | 0    | 10   | mV    |
|   |                   | E - F In dark condition                         | -10  | 0    | 10   | mV    |
|   |                   |   |      |      |      |       |
| Output voltage (note 1-2, 4)            | V <sub>O</sub>    | A~D Po=10μW, λ =780nm                           | 29.0 | 37.0 | 45.0 | mV/μW |
|   |                   | E, F Po=10μW, λ =780nm                          | 61.0 | 77.0 | 93.0 | mV/μW |
| Maximum output voltage<br>(note 1-3, 4) | V <sub>OMAX</sub> | A-D Po=100μW, λ =780nm                          | 3.9  | 4.1  |      | V     |
|   |                   | E, F Po=100μW, λ =780nm                         | 4.5  | 4.9  |      | V     |
| Frequency characteristics<br>(note 1-4) | f <sub>c</sub>    | A~D Po=10μW, λ =780nm<br>100kHz reference, -3dB | 6.0  | 8.0  |      | MHz   |
|   |                   | E, F Po=10μW, λ =780nm<br>10kHz reference, -3dB | 0.5  | 2.0  |      | MHz   |

note1-1 : Measure output offset voltage A to F with reference to V<sub>C</sub>.

note1-2 : Measure output voltage with reference to output offset voltage.

note1-3 : Measure maximum output voltage with reference to GND.

note1-4 : Output voltage, Frequency characteristics and Maximum output voltage are guaranteed by design.

## Electrical Characteristics (Except where noted otherwise Ta=25°C, Vcc=3V, Vc=1.5V)

| Item                                    | Symbol             | Measurement conditions                         | Min. | Typ. | Max. | Units |
|---|--------------------|--|------|------|------|-------|
| Current consumption                     | I <sub>CC</sub>    | In dark condition                              |      | 3.5  | 5.5  | mA    |
| Output offset voltage<br>(note 2-1)     | V <sub>OFF</sub>   | A~D In dark condition                          | -10  | 0    | 10   | mV    |
|   |                    | E, F In dark condition                         | -10  | 0    | 10   | mV    |
| Output offset<br>voltage difference     | $\Delta V_{OFF}$   | (A+B) - (C+D) In dark condition                | -10  | 0    | 10   | mV    |
|   |                    | (A+C) - (B+D) In dark condition                | -10  | 0    | 10   | mV    |
|   |                    | (A+D) - (B+C) In dark condition                | -10  | 0    | 10   | mV    |
|   |                    | E - F In dark condition                        | -10  | 0    | 10   | mV    |
| Output voltage (note 2-2, 4)            | V <sub>O</sub>     | A~D Po=10μW, λ=780nm                           | 29.0 | 37.0 | 45.0 | mV/μW |
|   |                    | E, F Po=10μW, λ=780nm                          | 61.0 | 77.0 | 93.0 | mV/μW |
| Maximum output voltage<br>(note 2-3, 4) | V <sub>omax.</sub> | A~D Po=100μW, λ=780nm                          | 1.9  | 2.1  |      | V     |
|   |                    | E, F Po=100μW, λ=780nm                         | 2.5  | 2.9  |      | V     |
| Frequency characteristics<br>(note 2-4) | f <sub>C</sub>     | A~D Po=10μW, λ=780nm<br>100kHz reference, -3dB | 6.0  | 8.0  |      | MHz   |
|   |                    | E, F Po=10μW, λ=780nm<br>10kHz reference, -3dB | 0.5  | 2.0  |      | MHz   |

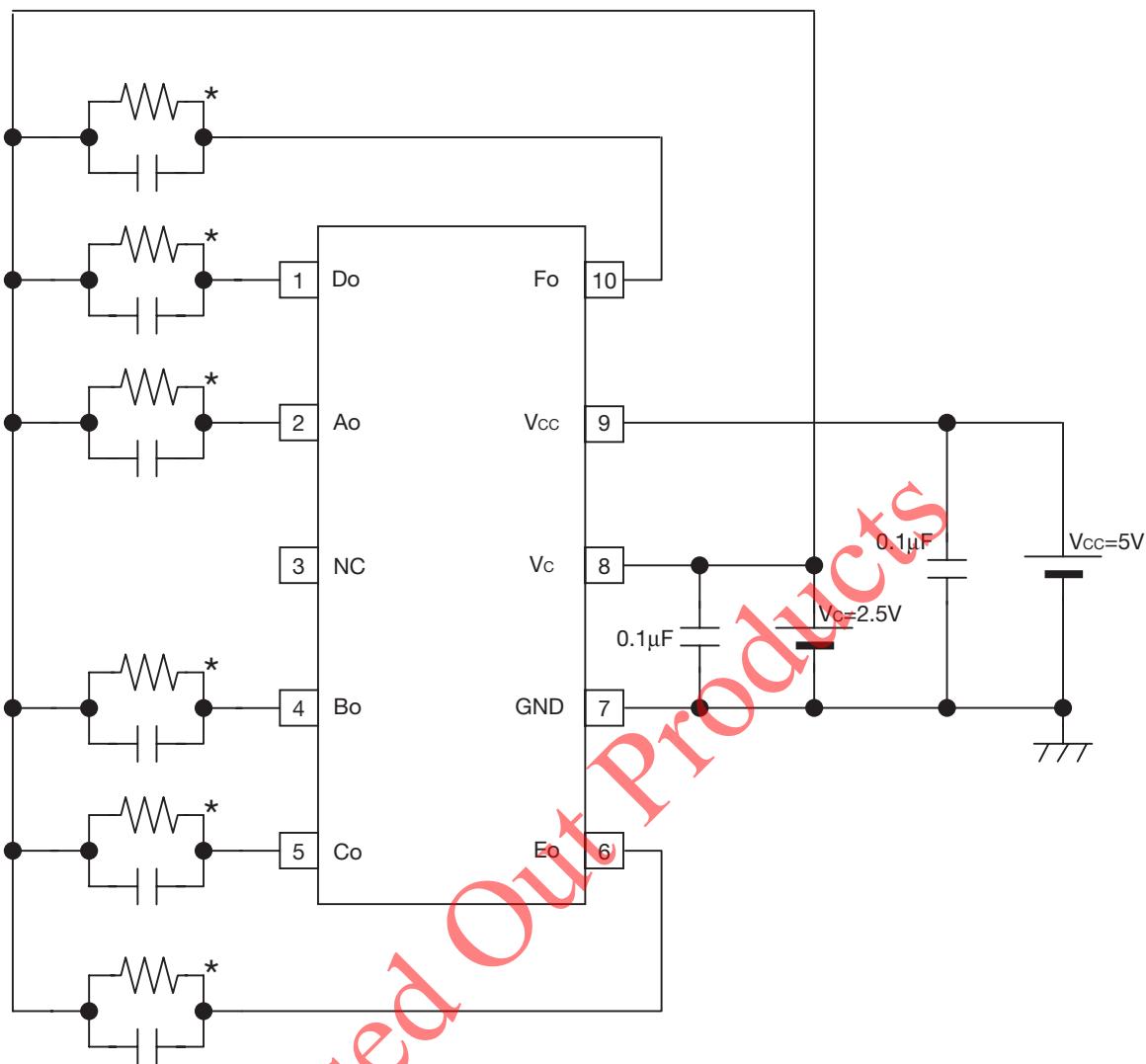
note2-1 : Measure output offset voltage A to F with reference to Vc.

note2-2 : Measure output voltage with reference to output offset voltage.

note2-3 : Measure maximum output voltage with reference to GND.

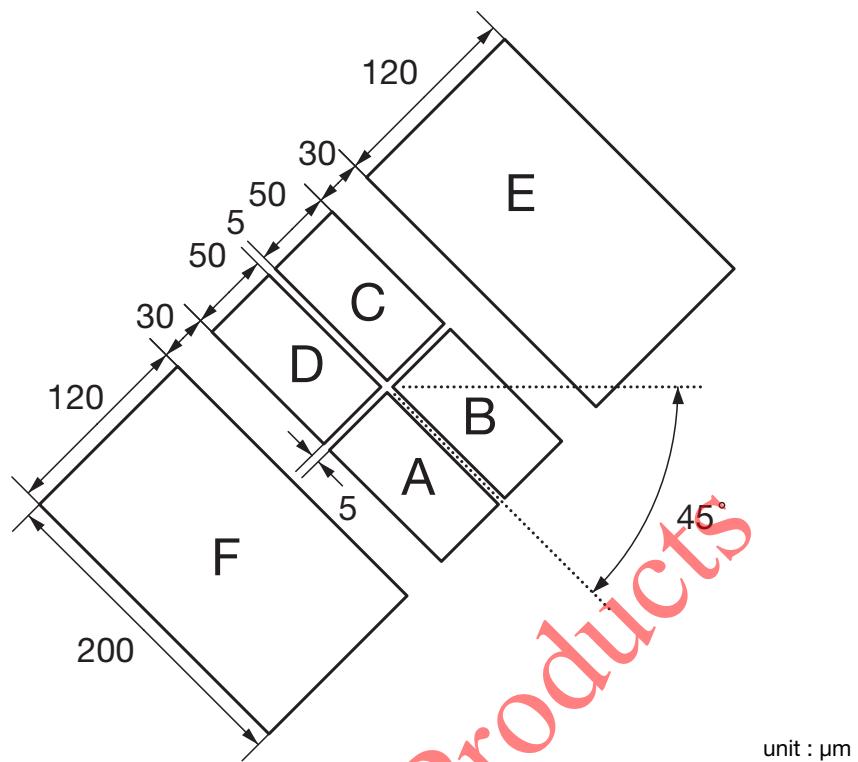
note2-4 : Output voltage, Frequency characteristics and Maximum output voltage are guaranteed by design.

## Measuring Circuit



\*Condition of load are all  $R_L : 10k\Omega$  //  $C_L : 10pF$

## Photo detector pattern dimensions



## Photo detector position

